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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 33x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5602df1vll3

3.6 Functional ports

The functional port pins are listed in Table 5.

Table 5. Functional port pin descriptions

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
Port A									
PA[0]	PCR[0]	AF0 AF1 AF2 AF3 —	GPIO[0] E0UC[0] CLKOUT E0UC[13] WKPU[19][3]	SIUL eMIOS_0 CGL eMIOS_0 WKPU	I/O I/O O I/O I	M	Tristate	5	12
PA[1]	PCR[1]	AF0 AF1 AF2 AF3 — —	GPIO[1] E0UC[1] — — NMI[4] WKPU[2][3]	SIUL eMIOS_0 — — WKPU WKPU	I/O I/O — — I I	S	Tristate	4	7
PA[2]	PCR[2]	AF0 AF1 AF2 AF3 —	GPIO[2] E0UC[2] — MA[2] WKPU[3][3]	SIUL eMIOS_0 — ADC WKPU	I/O I/O — O I	S	Tristate	3	5
PA[3]	PCR[3]	AF0 AF1 AF2 AF3 — —	GPIO[3] E0UC[3] — CS4_0 EIRQ[0] ADC1_S[0]	SIUL eMIOS_0 — DSPI_0 SIUL ADC	I/O I/O — I/O I I	S	Tristate	43	68
PA[4]	PCR[4]	AF0 AF1 AF2 AF3 —	GPIO[4] E0UC[4] — CS0_1 WKPU[9][3]	SIUL eMIOS_0 — DSPI_1 WKPU	I/O I/O — I/O I	S	Tristate	20	29
PA[5]	PCR[5]	AF0 AF1 AF2 AF3	GPIO[5] E0UC[5] — —	SIUL eMIOS_0 — —	I/O I/O — —	M	Tristate	51	79
PA[6]	PCR[6]	AF0 AF1 AF2 AF3 —	GPIO[6] E0UC[6] — CS1_1 EIRQ[1]	SIUL eMIOS_0 — DSPI_1 SIUL	I/O I/O — I/O I	S	Tristate	52	80

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PA[7]	PCR[7]	AF0 AF1 AF2 AF3 — —	GPIO[7] E0UC[7] — — EIRQ[2] ADC1_S[1]	SIUL eMIOS_0 — — SIUL ADC	I/O I/O — — I I	S	Tristate	44	71
PA[8]	PCR[8]	AF0 AF1 AF2 AF3 — N/A[5]	GPIO[8] E0UC[8] E0UC[14] — EIRQ[3] ABS[0]	SIUL eMIOS_0 eMIOS_0 — SIUL BAM	I/O I/O — — I I	S	Input, weak pull-up	45	72
PA[9]	PCR[9]	AF0 AF1 AF2 AF3 N/A[5]	GPIO[9] E0UC[9] — CS2_1 FAB	SIUL eMIOS_0 — DSPI_1 BAM	I/O I/O — I/O I	S	Pull-down	46	73
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 —	GPIO[10] E0UC[10] — LIN2TX ADC1_S[2]	SIUL eMIOS_0 — LINFlex_2 ADC	I/O I/O — O I	S	Tristate	47	74
PA[11]	PCR[11]	AF0 AF1 AF2 AF3 — — —	GPIO[11] E0UC[11] — — EIRQ[16] ADC1_S[3] LIN2RX	SIUL eMIOS_0 — — SIUL ADC LINFlex_2	I/O I/O — — I I I	S	Tristate	48	75
PA[12]	PCR[12]	AF0 AF1 AF2 AF3 — —	GPIO[12] — — — EIRQ[17] SIN_0	SIUL — — — SIUL DSPI_0	I/O — — — I I	S	Tristate	22	31
PA[13]	PCR[13]	AF0 AF1 AF2 AF3	GPIO[13] SOUT_0 — CS3_1	SIUL DSPI_0 — DSPI_1	I/O O — I/O	M	Tristate	21	30
PA[14]	PCR[14]	AF0 AF1 AF2 AF3 —	GPIO[14] SCK_0 CS0_0 E0UC[0] EIRQ[4]	SIUL DSPI_0 DSPI_0 eMIOS_0 SIUL	I/O I/O I/O I/O I	M	Tristate	19	28

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PB[7]	PCR[23]	AF0 AF1 AF2 AF3 —	GPIO[23] — — — ADC1_P[3]	SIUL — — — ADC	I — — — I	I	Tristate	37	55
PB[8]	PCR[24]	AF0 AF1 AF2 AF3 — —	GPIO[24] — — — ADC1_S[4] WKPU[25][3]	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	30	39
PB[9]	PCR[25]	AF0 AF1 AF2 AF3 — —	GPIO[25] — — — ADC1_S[5] WKPU[26][3]	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	29	38
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — —	GPIO[26] — — — ADC1_S[6] WKPU[8][3]	SIUL — — — ADC WKPU	I/O — — — I I	J	Tristate	31	40
PB[11]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ADC1_S[12]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — I/O I	J	Tristate	38	59
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ADC1_X[0]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	39	61
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ADC1_X[1]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	40	63
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ADC1_X[2]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	41	65

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
Port D									
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 — —	GPIO[48] — — — WKPU[27][3] ADC1_P[4]	SIUL — — — WKPU ADC	I — — — I I	I	Tristate	—	41
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 — —	GPIO[49] — — — WKPU[28][3] ADC1_P[5]	SIUL — — — WKPU ADC	I — — — I I	I	Tristate	—	42
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 —	GPIO[50] — — — ADC1_P[6]	SIUL — — — ADC	I — — — I	I	Tristate	—	43
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 —	GPIO[51] — — — ADC1_P[7]	SIUL — — — ADC	I — — — I	I	Tristate	—	44
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 —	GPIO[52] — — — ADC1_P[8]	SIUL — — — ADC	I — — — I	I	Tristate	—	45
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 —	GPIO[53] — — — ADC1_P[9]	SIUL — — — ADC	I — — — I	I	Tristate	—	46
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 —	GPIO[54] — — — ADC1_P[10]	SIUL — — — ADC	I — — — I	I	Tristate	—	47
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 —	GPIO[55] — — — ADC1_P[11]	SIUL — — — ADC	I — — — I	I	Tristate	—	48

Table 10. Absolute maximum ratings (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{DD_BV}	SR	Voltage on VDD_BV (regulator supply) pin with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	V_{DD} – 0.3	V_{DD} + 0.3	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_ADC}	SR	Voltage on VDD_HV_ADC (ADC reference) pin with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	V_{DD} – 0.3	V_{DD} + 0.3	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	V_{DD} – 0.3	V_{DD} + 0.3	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
I_{AVGSEG}	SR	Sum of all the static I/O current within a supply segment[1]	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	70	mA
			V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	64	
I_{CORELV}	SR	Low voltage static current sink through VDD_BV	—	—	150	mA
$T_{STORAGE}$	SR	Storage temperature	—	–55	150	°C

[1] Supply segments are described in Section 4.7.5, I/O pad current specification.

NOTE

Stresses exceeding the recommended absolute maximum ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During overload conditions ($V_{IN} > V_{DD}$ or $V_{IN} < V_{SS}$), the voltage on pins with respect to ground (V_{SS}) must not exceed the recommended values.

4.5 Recommended operating conditions

Table 11. Recommended operating conditions (3.3 V)

Symbol		C	Parameter	Conditions	Value		Unit
					Min	Max	
V_{SS}	SR	—	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}[1]	SR	—	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	3.0	3.6	V
V_{SS_LV}[2]	SR	—	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V

Table 11. Recommended operating conditions (3.3 V) (continued)

Symbol		C	Parameter	Conditions	Value		Unit
					Min	Max	
V_{DD_BV}[3]	SR	—	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	3.0	3.6	V
				Relative to V_{DD}	$V_{DD} - 0.1$	$V_{DD} + 0.1$	
V_{SS_ADC}	SR	—	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})	—	$V_{SS} - 0.1$	$V_{SS} + 0.1$	V
V_{DD_ADC}[4]	SR	—	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	3.0[5]	3.6	V
				Relative to V_{DD}	$V_{DD} - 0.1$	$V_{DD} + 0.1$	
V_{IN}	SR	—	Voltage on any GPIO pin with respect to ground (V_{SS})	—	$V_{SS} - 0.1$	—	V
				Relative to V_{DD}	—	$V_{DD} + 0.1$	
I_{INJPAD}	SR	—	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	—	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
TV_{DD}	SR	—	V_{DD} slope to ensure correct power up[6]	—	—	0.25	V/µs
$T_{A\ C\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias	$f_{CPU} \leq 48$ MHz	–40	85	°C
$T_{J\ C\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	110	
$T_{A\ V\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias		–40	105	
$T_{J\ V\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	130	
$T_{A\ M\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias		–40	125	
$T_{J\ M\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	150	

1 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.

2 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.

3 470 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).

4 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.

5 Full electrical specification cannot be guaranteed when voltage drops below 3.0 V. In particular, ADC electrical characteristics and I/Os DC electrical specification may not be guaranteed. When voltage drops below V_{LVDHVL}, device is reset.

6 Guaranteed by device validation

Table 12. Recommended operating conditions (5.0 V)

Symbol		C	Parameter	Conditions	Value		Unit
					Min	Max	
V_{SS}	SR	—	Digital ground on VSS_HV pins	—	0	0	V

Table 12. Recommended operating conditions (5.0 V) (continued)

Symbol		C	Parameter	Conditions	Value		Unit
					Min	Max	
V_{DD}[1]	SR	—	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	4.5	5.5	V
				Voltage drop[2]	3.0	5.5	
V_{SS_LV}[3]	SR	—	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_BV}[4]	SR	—	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	4.5	5.5	V
				Voltage drop(2)	3.0	5.5	
				Relative to V_{DD}	V_{DD} – 0.1	V_{DD} + 0.1	
V_{SS_ADC}	SR	—	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS}	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_ADC}[5]	SR	—	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	4.5	5.5	V
				Voltage drop(2)	3.0	5.5	
				Relative to V_{DD}	V_{DD} – 0.1	V_{DD} + 0.1	
V_{IN}	SR	—	Voltage on any GPIO pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	—	V
				Relative to V_{DD}	—	V_{DD} + 0.1	
I_{INJPAD}	SR	—	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	—	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
TV_{DD}	SR	—	V_{DD} slope to ensure correct power up[6]	—	—	0.25	V/µs
$T_{A\ C\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias	$f_{CPU} \leq 48$ MHz	–40	85	°C
$T_{J\ C\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	110	
$T_{A\ V\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias		–40	105	
$T_{J\ V\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	130	
$T_{A\ M\text{-}Grade\ Part}$	SR	—	Ambient temperature under bias		–40	125	
$T_{J\ M\text{-}Grade\ Part}$	SR	—	Junction temperature under bias		–40	150	

1 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.

2 Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.6 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.

3 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.

4 470 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).

5 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.

6 Guaranteed by device validation

$$T_J = T_A + (P_D \times R_{\theta JA})$$ *Eqn. 1*

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273\ °C)$$ *Eqn. 2*

Therefore, solving equations 1 and 2:

$$K = P_D \times (T_A + 273\ °C) + R_{\theta JA} \times P_D^2$$ *Eqn. 3*

Where:

K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A.

4.7 I/O pad electrical characteristics

4.7.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads—These pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads—These pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Input only pads—These pads are associated to ADC channels (ADC_P[X]) providing low input leakage.

Medium pads can use slow configuration to reduce electromagnetic emission except for PC[1], that is medium only, at the cost of reducing AC performance.

4.7.2 I/O input DC characteristics

Table 14 provides input DC electrical characteristics as described in Figure 4.

- Table 16 provides output driver characteristics for I/O pads when in SLOW configuration.
- Table 17 provides output driver characteristics for I/O pads when in MEDIUM configuration.

Table 15. I/O pull-up/pull-down DC electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
$\|I_{WPU}\|$	CC	P	Weak pull-up current absolute value	$V_{IN} = V_{IL}$, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1[2]	10	—	250	
		P		$V_{IN} = V_{IL}$, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	
$\|I_{WPD}\|$	CC	P	Weak pull-down current absolute value	$V_{IN} = V_{IH}$, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1[(2)]	10	—	250	
		P		$V_{IN} = V_{IH}$, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 16. SLOW configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	P	Output high level SLOW configuration	Push Pull	I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V_{DD} – 0.8	—	—	
V_{OL}	CC	P	Output low level SLOW configuration	Push Pull	I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
		C			I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[(2)]	—	—	$0.1V_{DD}$	
		C			I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 20. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value Min	Value Typ	Value Max	Unit
I_{SWTSLW},[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}(2)	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	
I_{RMSMED}	CC	D	Root mean square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.6	mA
				C_L = 25 pF, 40 MHz		—	—	13.4	
				C_L = 100 pF, 13 MHz		—	—	18.3	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	5	
				C_L = 25 pF, 40 MHz		—	—	8.5	
				C_L = 100 pF, 13 MHz		—	—	11	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		—	—	65	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

Table 21 provides the weight of concurrent switching I/Os.

In order to ensure device functionality, the sum of the weight of concurrent switching I/Os on a single segment should remain below 100%.

Table 21. I/O weight[1] (continued)

Pad	100 LQFP/64 LQFP			
	Weight 5 V		Weight 3.3 V	
	SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1
PC[0]	6%	9%	7%	8%
PE[2]	7%	10%	8%	9%
PE[3]	7%	10%	9%	9%
PC[5]	8%	11%	9%	10%
PC[4]	8%	11%	9%	10%
PE[4]	8%	12%	10%	10%
PE[5]	8%	12%	10%	11%
PE[6]	9%	12%	10%	11%
PE[7]	9%	12%	10%	11%
PC[12]	9%	13%	11%	11%
PC[13]	9%	9%	11%	11%
PC[8]	9%	9%	11%	11%
PB[2]	9%	13%	11%	12%

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless specified

2 SRC: “Slew Rate Control” bit in SIU_PCR

4.8 RESET electrical characteristics

The device implements a dedicated bidirectional RESET pin.

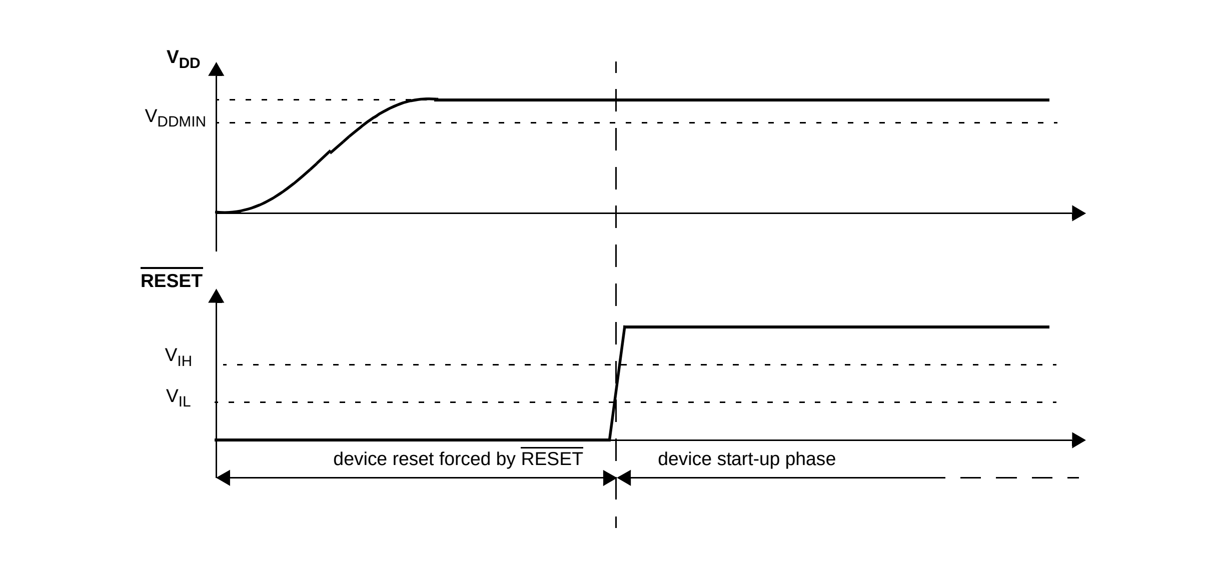


Figure 5. Start-up reset requirements

— LV_CFLA: Low voltage supply for code flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
— LV_DFLA: Low voltage supply for data flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
— LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

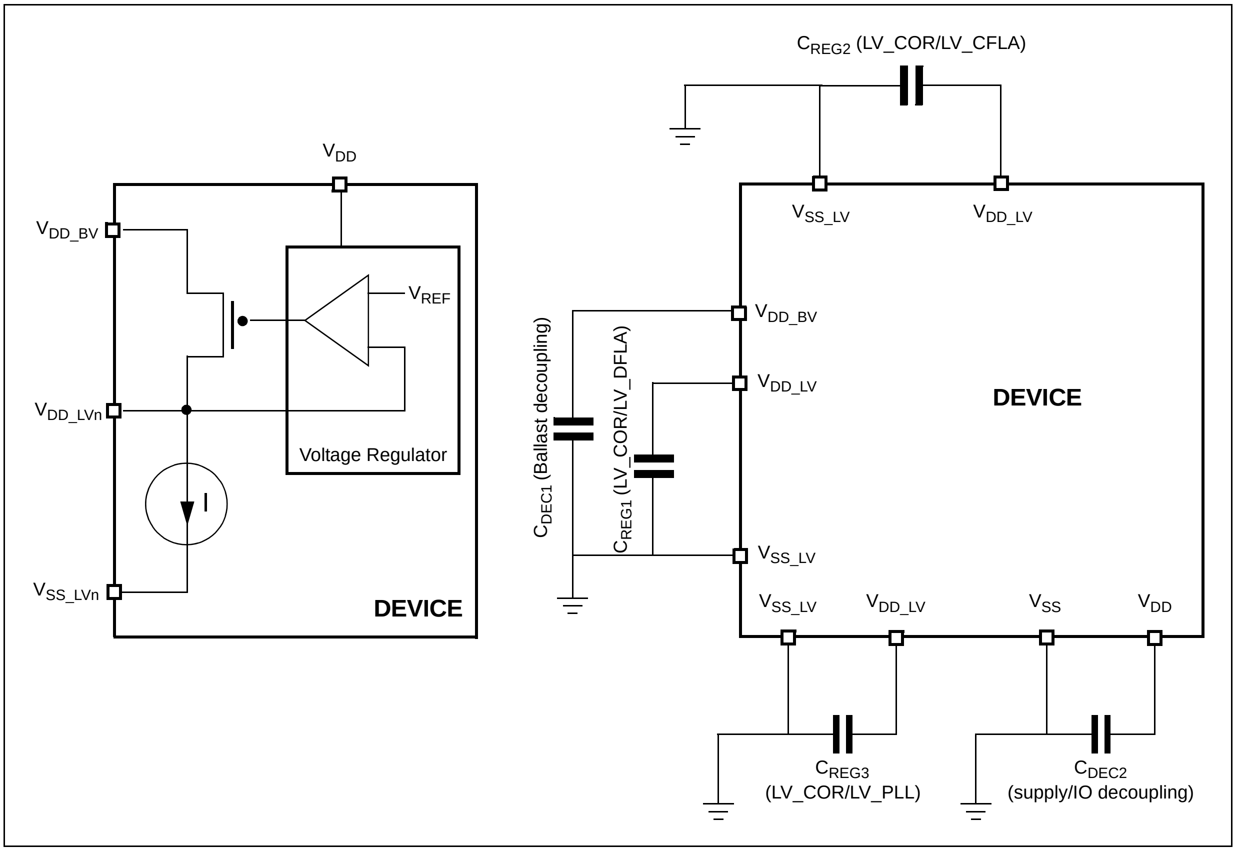


Figure 7. Voltage regulator capacitance connection

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

Each decoupling capacitor must be placed between each of the three V_{DD_LV}/V_{SS_LV} supply pairs to ensure stable voltage (see Section 4.5, Recommended operating conditions).

Table 23. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
C_{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	Ω

4.9.2 Low voltage detector electrical characteristics

The device implements a power-on reset (POR) module to ensure correct power-up initialization, as well as five low voltage detectors (LVDs) to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

- POR monitors V_{DD} during the power-up phase to ensure device is maintained in a safe reset state (refer to RGM Destructive Event Status (RGM_DES) Register flag F_POR in device reference manual)
- LVDHV3 monitors V_{DD} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27 in device reference manual)
- LVDHV3B monitors V_{DD_BV} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27_VREG in device reference manual)
- LVDHV5 monitors V_{DD} when application uses device in the 5.0 V ± 10% range (refer to RGM Functional Event Status (RGM_FES) Register flag F_LVD45 in device reference manual)
- LVDLVCOR monitors power domain No. 1 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD1 in device reference manual)
- LVDLVBKP monitors power domain No. 0 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD0 in device reference manual)

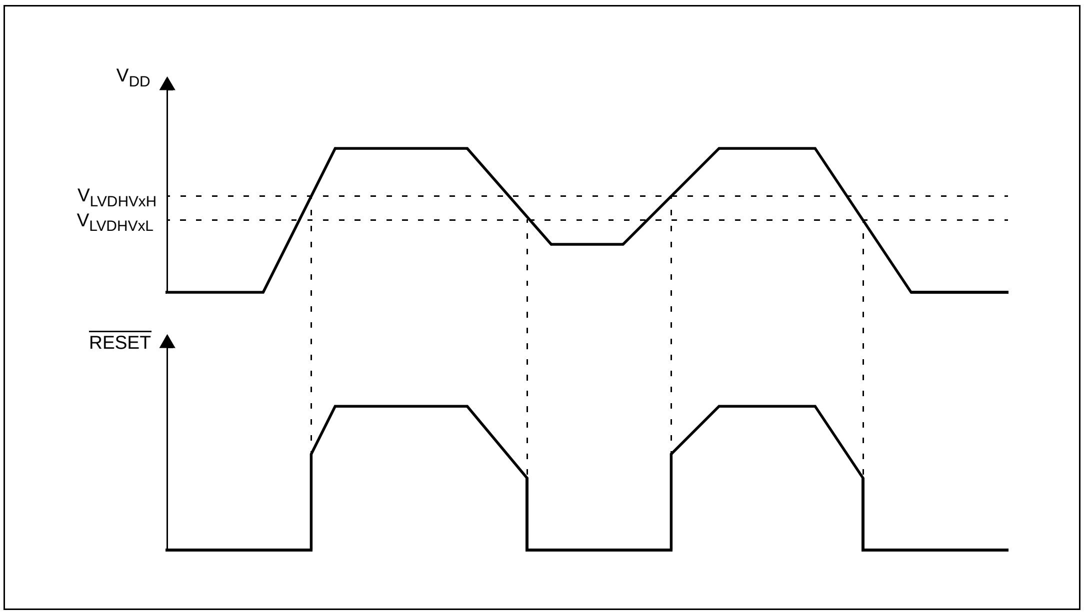


Figure 8. Low voltage detector vs reset

Table 33. ESD absolute maximum ratings[1] [2]

Symbol		C	Ratings	Conditions	Class	Max value	Unit
$V_{ESD(HBM)}$	CC	T	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	CC	T	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	V
$V_{ESD(CDM)}$	CC	T	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	V
						750 (corners)	V

1 All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

2 A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

4.12.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

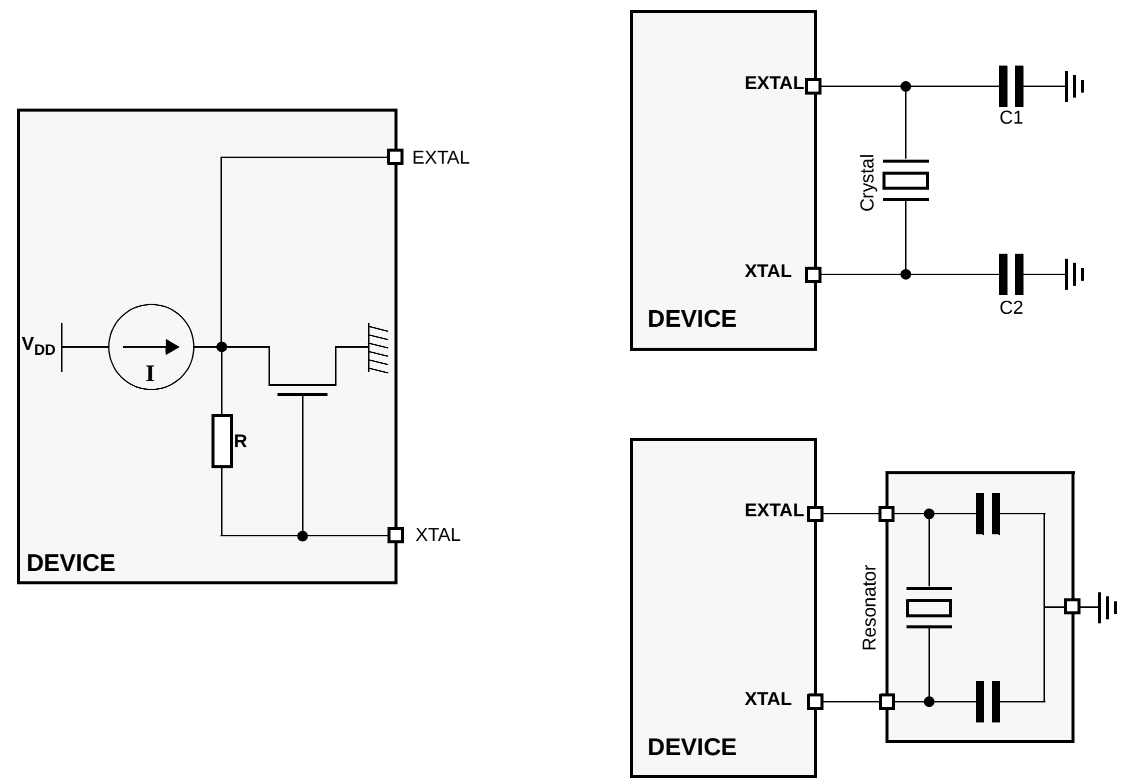
Table 34. Latch-up results

Symbol		C	Parameter	Conditions	Class
LU	CC	T	Static latch-up class	T_A = 125 °C conforming to JESD 78	II level A

4.13 Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

The device provides an oscillator/resonator driver. Figure 9 describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 35 provides the parameter description of 4 MHz to 16 MHz crystals used for the design simulations.



Notes:
1. XTAL/EXTAL must not be directly used to drive external circuits
2. A series resistor may be required, according to crystal oscillator supplier recommendations.

Figure 9. Crystal oscillator and resonator connection scheme

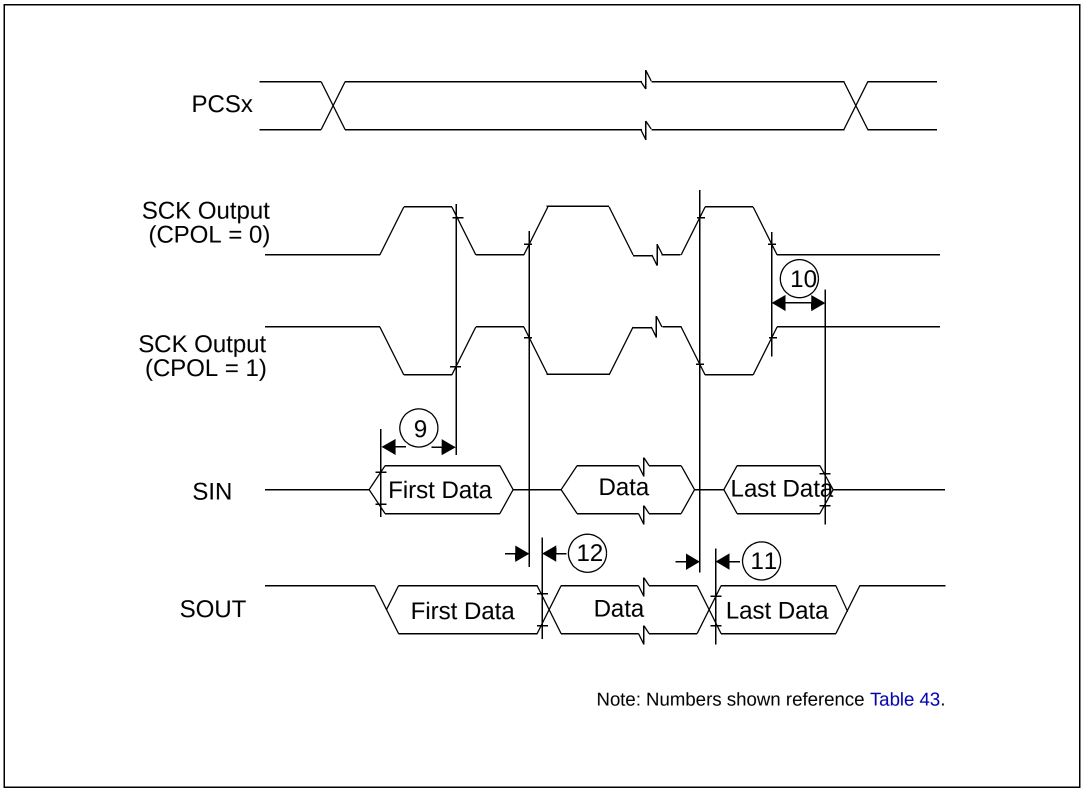


Figure 17. DSPI classic SPI timing – master, CPHA = 1

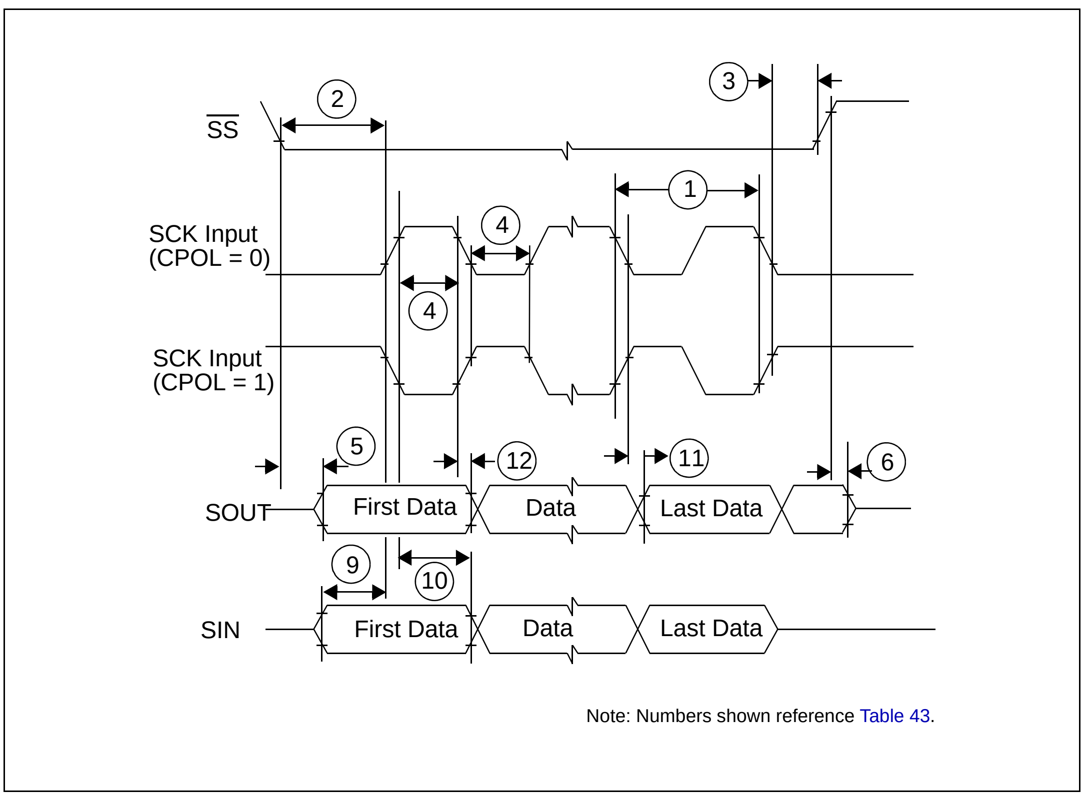


Figure 18. DSPI classic SPI timing – slave, CPHA = 0

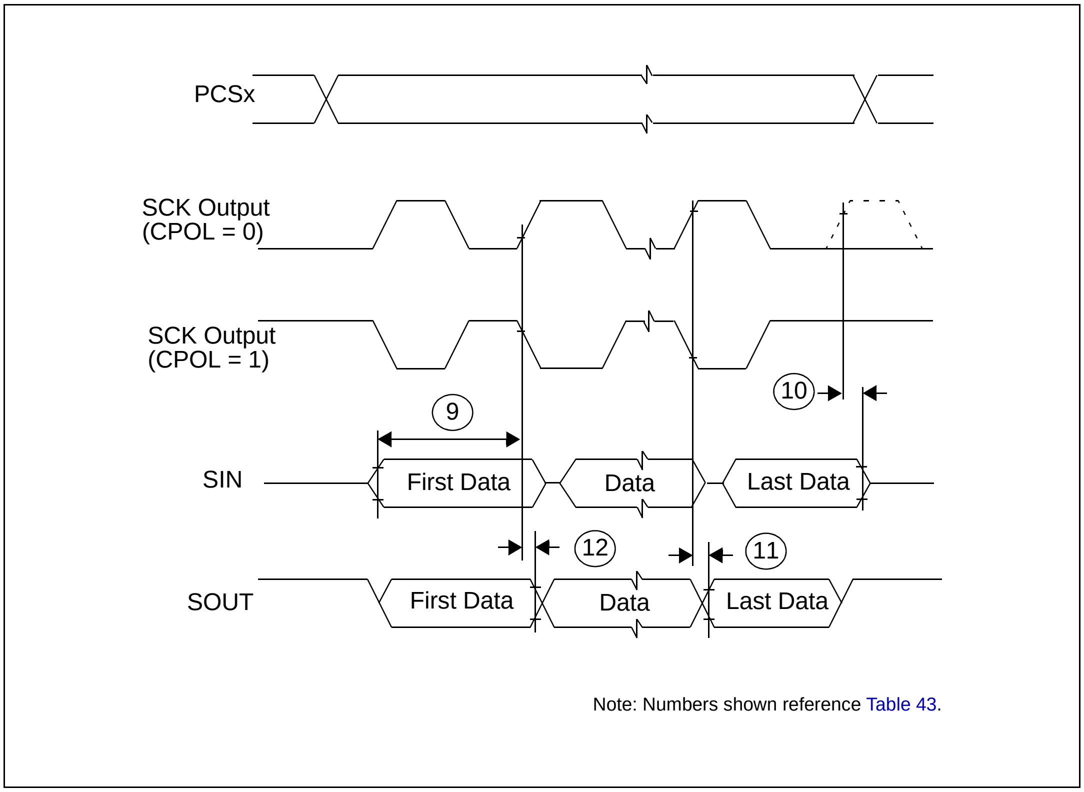


Figure 21. DSPI modified transfer format timing – master, CPHA = 1

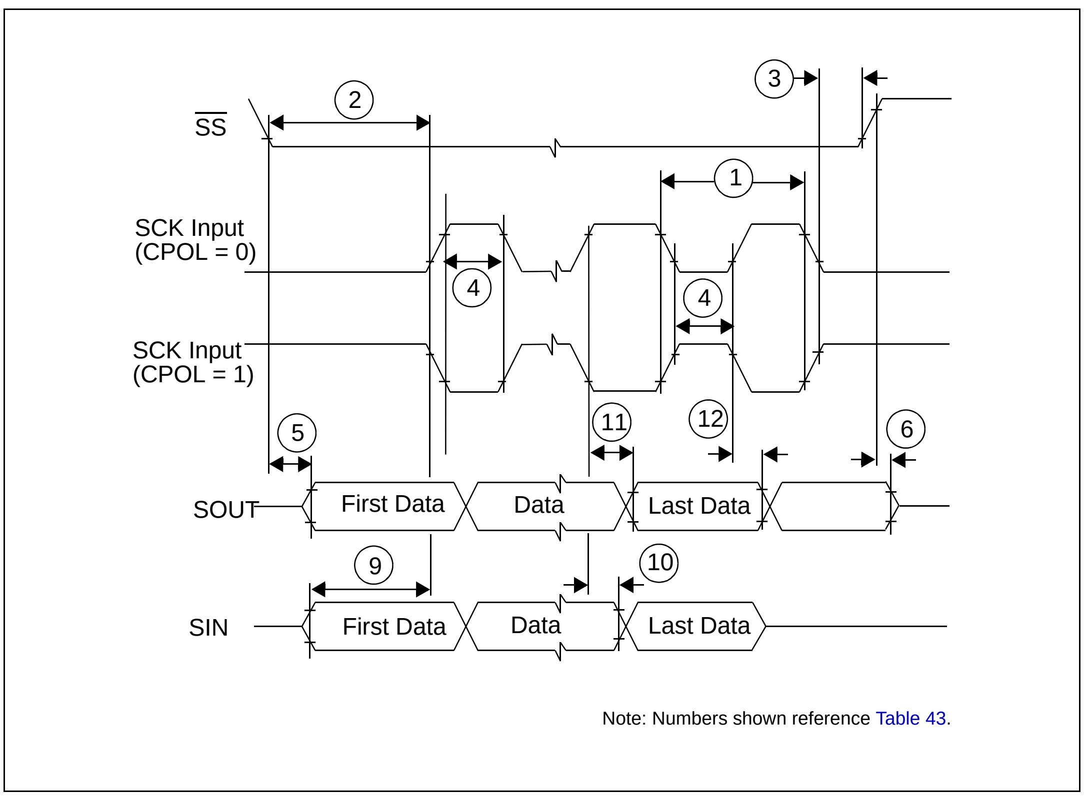


Figure 22. DSPI modified transfer format timing – slave, CPHA = 0

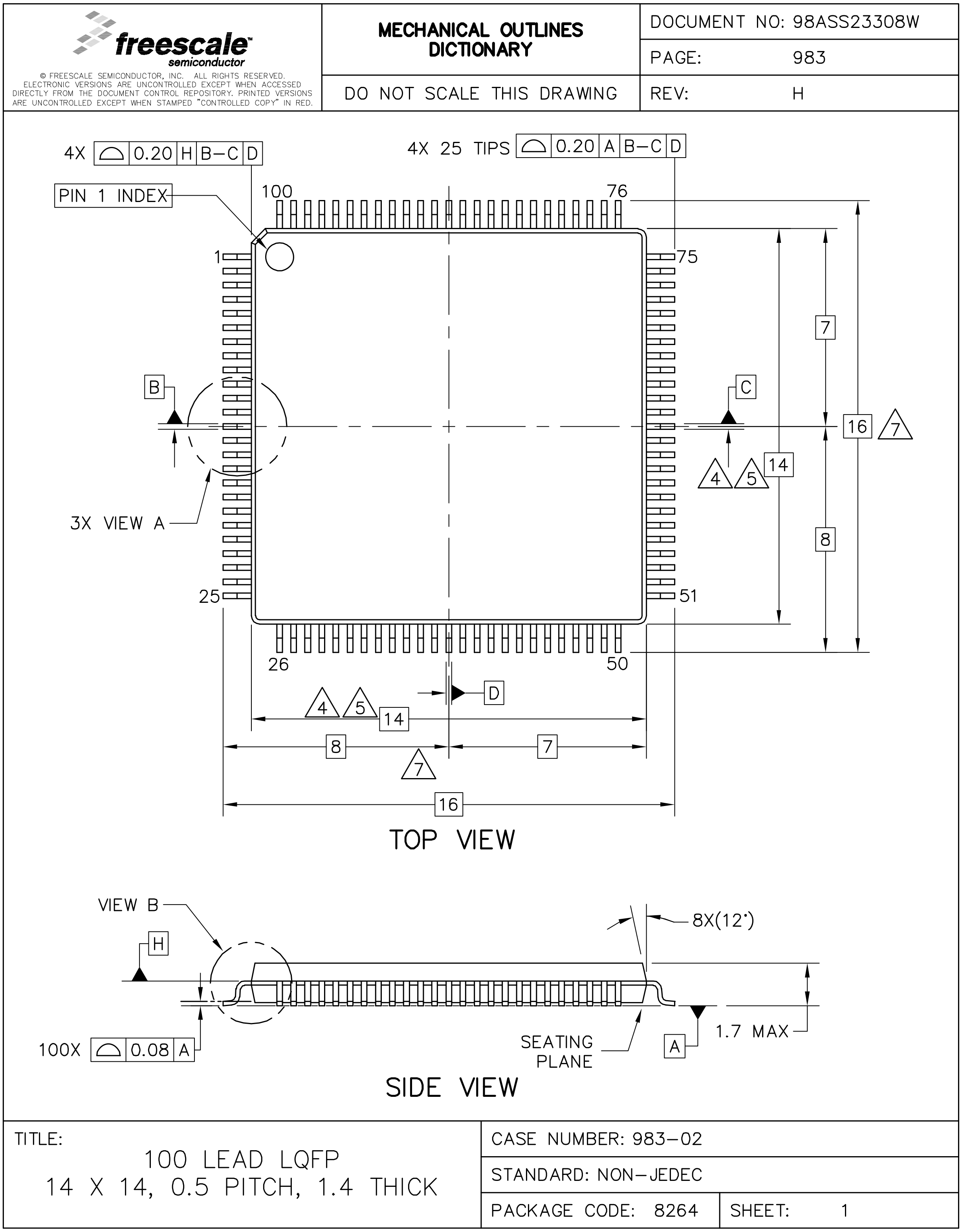


Figure 26. 100 LQFP package mechanical drawing (Part 1 of 3)

Table A-1. Abbreviations (continued)

Abbreviation	Meaning
OPWMCB	Center aligned output pulse width modulation buffered with dead time
OPWMT	Output pulse width modulation trigger
PWM	Pulse width modulation
SAIC	Single action input capture
SAOC	Single action output compare
SCK	Serial communications clock
SOUT	Serial data out
TBD	To be defined
TCK	Test clock input
TDI	Test data input
TDO	Test data output
TMS	Test mode select

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